

AMENDMENTS TO THE CLAIMS:

1. (Currently Amended) A semiconductor device having only one wiring layer including a plurality of [wirings] wires juxtaposed with one another and a first SiOF insulating film being in contact with the [wirings] wires, characterized in that the fluorine concentration of the first SiOF insulating film at a [wiring] wire gap portion is set to be higher than the fluorine concentration of a second SiOF insulating film on [the] an upper side of the [wirings] wires, wherein the first SiOF insulating film is in contact with the [wirings] wires only at the [wiring] wire gap portion and is not in contact with the upper side of the [wirings] wires, and the second SiOF insulating film is in contact with both the first SiOF insulating film and the upper sides of the wires.

2. (Canceled)

3. (Currently Amended) The semiconductor device as claimed in claim 1, wherein the thickness of the first SiOF insulating film at a center of the [wiring] wire gap portion is within the range of 1/3 to 1/1 times of the thickness of the [wirings] wires.

4. (Currently Amended) The semiconductor device as claimed in claim 1, wherein the fluorine concentration of the first SiOF insulating film is set to 5 atom % or more, and the fluorine concentration of the second SiOF insulating film is set to be less than 5 atom %.

5. (Currently Amended) A semiconductor device having a plurality of wiring layers each having a plurality of [wirings] wires juxtaposed with one another and a first SiOF interlayer insulating film, characterized in that the fluorine concentration of the first SiOF

interlayer insulating film at a [wiring] wire gap portion is set to be higher than the fluorine concentration of a second SiOF interlayer insulating film on [the] an upper side of the [wirings] wires, wherein the first SiOF interlayer insulating film is in contact with the [wirings] wires only at the [wiring] wire gap portion and is not in contact with the upper side of the [wirings] wires, and the second SiOF interlayer insulating film is in contact with both the first SiOF interlayer insulating film and the upper side of the wires.

6. (Canceled)

7. (Currently Amended) The semiconductor device as claimed in claim 5, wherein the thickness of the first SiOF interlayer insulating film at a center of the [wiring] wire gap portion is within the range of 1/3 to 1/1 times of the thickness of the [wirings] wires.

8. (Currently Amended) The semiconductor device as claimed in claim 5, wherein the fluorine concentration of the first SiOF interlayer insulating film is set to 5 atom % or more, and the fluorine concentration of the second SiOF interlayer insulating film is set to be less than 5 atom %.

Claims 9-14 (canceled).

15. (New) The semiconductor device as claimed in claim 1, wherein the first SiOF insulating film is in contact with the second SiOF insulating film only at the wire gap portion.

16. (New) The semiconductor device as claimed in claim 15, wherein the thickness of the first SiOF insulating film at a center of the wire gap portion is within the range of 1/3 to 1/1 times of the thickness of the wires.

17. (New) The semiconductor device as claimed in claim 15, wherein the fluorine concentration of the first SiOF insulating film is set to 5 atom% or more, and the fluorine concentration of the second SiOF insulating film is set to be less than 5 atom %.

18. (New) The semiconductor device as claimed in claim 5, wherein the first SiOF interlayer insulating film is in contact with the second SiOF interlayer insulating film only at the wire gap portion.

19. (New) The semiconductor device as claimed in claim 18, wherein the thickness of the first SiOF interlayer insulating film at a center of the wire gap portion is within the range of 1/3 to 1/1 times of the thickness of the wires.

20. (New) The semiconductor device as claimed in claim 18, wherein the fluorine concentration of the first SiOF interlayer insulating film is set to 5 atom % or more, and the fluorine concentration of the second SiOF interlayer insulating film is set to be less than 5 atom %.